## Source coupled MOSFET pair (differential MOSFET pair)



Function

- The input current $I_{0}$ is split into $I_{D 1}$ and $I_{D 2}$, according to fractions $x$ and (1-x)
- $x$ depends on $V_{D}\left(x=0.5\right.$ for $\left.V_{D}=0\right)$

Inputs: $V_{1}, V_{2}$ (effective input signal: $V_{D}=V_{1}-V_{2}$ ) $I_{0}$ ("Tail current")

Outputs: $I_{D 1}, I_{D 2}\left(I_{D 1}-I_{D 2}\right)$


Analysis of the source coupled MOSFET pair (differential MOSFET pair)


Target: obtain the relationship between the ratio $x$ and the input differential voltage $V_{D}$

$$
I_{D 1}=x I_{0} \quad I_{D 2}=(1-x) I_{0} \quad \square x \triangleq \frac{I_{D 1}}{I_{0}}
$$

Hypotheses

- M1 and M2 work in saturation and the effect of $V_{D S}$ can be neglected
- Strong inversion equation can be applied
- $I_{0}$ does not depend on $V_{1}, V_{2}$
$I_{0}$ has been represented as an ideal current source placed between M1, M2 sources and $\mathrm{V}_{\mathrm{SS}}$ : this is just an example.

$$
I_{D}=\frac{\beta}{2}\left(V_{G S}-V_{t}\right)^{2} \Rightarrow V_{G S}=V_{t}+\sqrt{\frac{2 I_{D}}{\beta}}
$$

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$$
\begin{aligned}
& \left\{\begin{array}{l}
V_{1}=V_{S 1}+V_{G S 1} \\
V_{2}=V_{S 2}+V_{G S 2}
\end{array} \quad V_{S 1}=V_{S 2} \triangleq V_{S}\right. \\
& V_{D}=V_{1}-V_{2}=V_{G S 1}-V_{G S 2} \\
& V_{D}=V_{t 1}+\sqrt{\frac{2 I_{D 1}}{\beta_{1}}}-\left(V_{t 2}+\sqrt{\frac{2 I_{D 2}}{\beta_{2}}}\right)
\end{aligned}
$$

Nominal conditions: $\mathrm{M} 1=\mathrm{M} 2: \beta_{1}=\beta_{2}=\beta$ and $V_{t 1}=V_{t 2} \quad\left(V_{B S 1}=V_{B S 2}\right)$.

$$
V_{D}=\sqrt{\frac{2 I_{D 1}}{\beta}}-\sqrt{\frac{2 I_{D 2}}{\beta}}=\sqrt{\frac{2}{\beta}} \cdot\left(\sqrt{I_{D 1}}-\sqrt{I_{D 2}}\right)
$$

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$$
\begin{aligned}
x= & \frac{1}{2} \pm \frac{1}{2} \sqrt{2\left(\frac{V_{D}}{V_{D M A X}}\right)^{2}-\left(\frac{V_{D}}{V_{D M A X}}\right)^{4}}=\frac{1}{2} \pm \frac{1}{2}\left(\frac{V_{D}}{V_{D M A X}}\right) \sqrt{2-\left(\frac{V_{D}}{V_{D M A X}}\right)^{2}} \\
& \text { condition } 1 \quad V_{D}>0 \Rightarrow x>\frac{1}{2}
\end{aligned}
$$

$$
\left\{\begin{array} { l } 
{ x = \frac { I _ { D 1 } } { I _ { 0 } } = \frac { 1 } { 2 } + \frac { 1 } { 2 } ( \frac { V _ { D } } { V _ { D M A X } } ) \sqrt { 2 - ( \frac { V _ { D } } { V _ { D M A X } } ) ^ { 2 } } } \\
{ 1 - x = \frac { I _ { D 2 } } { I _ { 0 } } = \frac { 1 } { 2 } - \frac { 1 } { 2 } ( \frac { V _ { D } } { V _ { D M A X } } ) \sqrt { 2 - ( \frac { V _ { D } } { V _ { D M A X } } ) ^ { 2 } } }
\end{array} \Rightarrow \left\{\begin{array}{l}
I_{D 1}=\frac{I_{0}}{2}+\frac{I_{0}}{2}\left(\frac{V_{D}}{V_{D M A X}}\right) \sqrt{2-\left(\frac{V_{D}}{V_{D M A X}}\right)^{2}} \\
I_{D 2}=\frac{I_{0}}{2}-\frac{I_{0}}{2}\left(\frac{V_{D}}{V_{D M A X}}\right) \sqrt{2-\left(\frac{V_{D}}{V_{D M A X}}\right)^{2}}
\end{array}\right.\right.
$$



$$
\left(\frac{V_{D}}{V_{D M A X}}\right)^{2}-1 \leq 0
$$

condition 2
The analysis is applicable only between $-\mathrm{V}_{\mathrm{DMAX}}$ and $+\mathrm{V}_{\mathrm{DMAX}}$

$$
\begin{aligned}
& I_{D 1}=\frac{I_{0}}{2}+\frac{I_{0}}{2}\left(\frac{V_{D}}{V_{D M A X}}\right) \sqrt{2-\left(\frac{V_{D}}{V_{D M A X}}\right)^{2}} \\
& I_{D 2}=\frac{I_{0}}{2}-\frac{I_{0}}{2}\left(\frac{V_{D}}{V_{D M A X}}\right) \sqrt{2-\left(\frac{V_{D}}{V_{D M A X}}\right)^{2}}
\end{aligned}
$$

$$
V_{D}=-V_{D M A X} \Rightarrow I_{D 1}=0
$$

$$
V_{D}=0 \Rightarrow I_{D 1}=\frac{I_{0}}{2}
$$

## Derivative of the differential pair input-output curves (optional)

$$
\begin{gathered}
I_{D 1}=\frac{I_{0}}{2}+\frac{I_{0}}{2}\left(\frac{V_{D}}{V_{D M A X}}\right) \sqrt{2-\left(\frac{V_{D}}{V_{D M A X}}\right)^{2}}=\frac{I_{0}}{2}\left[1+z \sqrt{2-z^{2}}\right] \text { with } z=\left(\frac{V_{D}}{V_{D M A X}}\right) \\
\frac{d I_{D 1}}{d V_{D}}=\frac{I_{0}}{2 V_{D M A X}}\left[\sqrt{2-z^{2}}-\frac{2 z^{2}}{2 \sqrt{2-z^{2}}}\right]=\frac{I_{0}}{2 V_{D M A X}} \frac{2-z^{2}-z^{2}}{\sqrt{2-z^{2}}}=\frac{I_{0}}{V_{D M A X}} \frac{1-z^{2}}{\sqrt{2-z^{2}}} \\
\hdashline V_{D}=0 \Rightarrow \frac{d I_{D 1}}{d V_{D}}=\frac{I_{0}}{\sqrt{2} V_{D M A X}}=\sqrt{\frac{I_{0}^{2} \beta}{4 I_{0}}}=\frac{1}{2} \sqrt{\beta I_{0}}
\end{gathered}
$$

Extrapolation outside the $-\mathrm{V}_{\mathrm{DMAX}} \leq \mathrm{V}_{\mathrm{D}} \leq \mathrm{V}_{\text {DMAX }}$ region


$$
V_{D}=V_{G S 1}-V_{G S 2} \Rightarrow V_{G S 2}=V_{G S 1}-V_{D}
$$

$$
\begin{aligned}
& \text { Considering the boundary: } \\
& V_{D}=V_{D M A X} \quad I_{D 1}=I_{0} \Rightarrow V_{G S 1}=V_{t}+\sqrt{\frac{2 I_{0}}{\beta}}
\end{aligned}
$$

$$
\left\{\begin{array}{l}
V_{G S 1}=V_{t}+V_{D M A X} \\
V_{G S 2}=V_{G S 1}-V_{D}=V_{t}
\end{array} \quad \text { If } \mathrm{V}_{\mathrm{D}} \text { increases over } \mathrm{V}_{\mathrm{DMAX}}:\right.
$$

$$
\mathrm{V}_{\text {GS1 }} \text { cannot increase because }
$$

$$
I_{D 1} \text { would become }>I_{0} \text {, which is }
$$ impossible.

Then $\mathrm{V}_{\mathrm{GS2}}$ gets smaller than $\mathrm{V}_{\mathrm{t}}$
$I_{D 2}$ keeps being $=0$
$I_{D 1}$ keeps being $=I_{0}$
The opposite occurs when $V_{D}$ decreases below $V_{D M A X}$ :
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Mosfet differential pair: parameters


For $V_{D}=0$ (typical operating point): $\quad I_{D 1}=I_{D 2} \triangleq I_{D Q}=\frac{I_{0}}{2}$
$V_{D M A X}=\sqrt{\frac{2 \cdot 2 I_{D Q}}{\beta}}=\sqrt{2} \sqrt{\frac{2 I_{D Q}}{\beta}}=\underline{\underline{\sqrt{2}\left(V_{G S}-V_{t}\right)_{Q}}}$
$\left.\frac{d I_{D 1}}{d V_{D}}\right|_{V_{D}=0}=\frac{1}{2} \sqrt{2 \beta I_{D Q}}=\frac{g_{m}}{2}$

## Small signal behavior

For small variations $\left(v_{d}\right)$ of $V_{D}$ around 0 :

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## Large-signal dependence of the source voltage on $V_{D}$


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## Differential output current



Mosfet differential pair: real curves (calculated) and linearity

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## BJT differential pair



## BJT differential pair

## BJT differential pair - small signal currents



## MOSFET and BJT differential pairs compared



In the mosfet pair, $\mathrm{V}_{\mathrm{DMAX}}$ can be varied by modifying $\beta$ and $I_{0}$

Paremeter $\mathrm{g}_{\mathrm{m}}$ depends on

$$
\begin{aligned}
& \text { both } I_{0} \text { and } \beta \text { : } \\
& g_{m}=\sqrt{\beta I_{0}} \quad V_{D M A X}=\sqrt{\frac{2 I_{0}}{\beta}}
\end{aligned}
$$

Note: a mosfet pair in subthreshold region behaves like a BJT pair with the substitution:

$$
m V_{T} \rightarrow V_{T}
$$

In the BJT pair, $\mathrm{V}_{\text {DMAX }}$ is fixed to around $4 \mathrm{~V}_{\mathrm{T}}$

Paremeter $\mathrm{g}_{\mathrm{m}}$ depends only on $I_{0}$

$$
g_{m}=\frac{I_{C Q}}{V_{T}}=\frac{I_{0}}{2 V_{T}}
$$

How to increase the $V_{D M A X}$ of a BJT pair

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